

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

# **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

# **General Purpose Transistors**

# **PNP Silicon**

# **Features**

• Pb-Free Packages are Available

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-60	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current - Continuous	Ic	-600	mAdc
Collector Current - Peak (Note 3)	I <sub>CM</sub>	-1200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

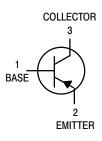
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
- 3. Reference SOA curve.



# ON Semiconductor®

# http://onsemi.com





SOT-23 (TO-236AB) CASE 318 STYLE 6

#### **MARKING DIAGRAM**



2F = Device Code M = Date Code\* • = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

# ORDERING INFORMATION

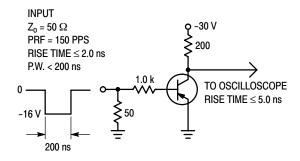
Device	Package	Shipping <sup>†</sup>
MMBT2907ALT1	SOT-23	3000 Tape & Reel
MMBT2907ALT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT2907ALT3	SOT-23	10,000 Tape & Reel
MMBT2907ALT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Charact	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (Note $(I_C = -1.0 \text{ mAdc}, I_B = 0)$ $(I_C = -10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)</sub> CEO	-60 -60	- -	Vdc	
Collector - Base Breakdown Voltage (I <sub>C</sub> =	-10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-60	-	Vdc
Emitter - Base Breakdown Voltage (I <sub>E</sub> = -	10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = −30 Vdc, V	V <sub>EB(off)</sub> = −0.5 Vdc)	I <sub>CEX</sub>	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	I <sub>CBO</sub>	- -	-0.010 -10	μAdc	
Base Cutoff Current (V <sub>CE</sub> = -30 Vdc, V <sub>EB</sub>	(off) = -0.5 Vdc)	I <sub>BL</sub>	1	-50	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \end{array} $	e 4)	h <sub>FE</sub>	75 100 100 100 50	- - - 300 -	-
Collector - Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (Note 4) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)		V <sub>CE(sat)</sub>		-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 4) $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	V <sub>BE(sat)</sub>	- -	-1.3 -2.6	Vdc	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note ( $I_C = -50 \text{ mAdc}$ , $V_{CE} = -20 \text{ Vdc}$ , $f = 100 \text{ mHz}$ )	. ,.	f <sub>T</sub>	200	-	MHz
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	_	8.0	pF
Input Capacitance (V <sub>EB</sub> = -2.0 Vdc, I <sub>C</sub> = 0	C <sub>ibo</sub>	-	30		
SWITCHING CHARACTERISTICS					
Turn-On Time		t <sub>on</sub>	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t <sub>d</sub>	-	10	
Rise Time	D1 - ····/	t <sub>r</sub>	-	40	
Turn-Off Time		t <sub>off</sub>	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t <sub>s</sub>	_	80	
Fall Time	.61 – .62 – (46)	t <sub>f</sub>	_	30	

- 4. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- 5.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.





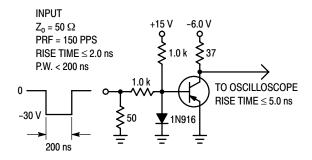


Figure 2. Storage and Fall Time Test Circuit

# **TYPICAL CHARACTERISTICS**

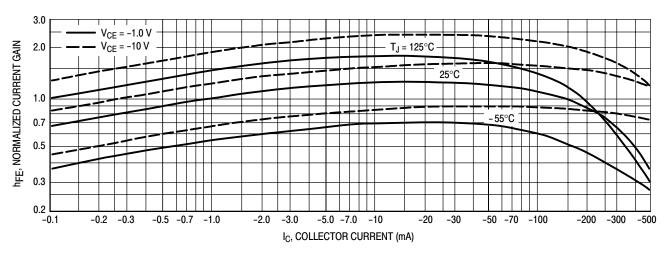


Figure 3. DC Current Gain

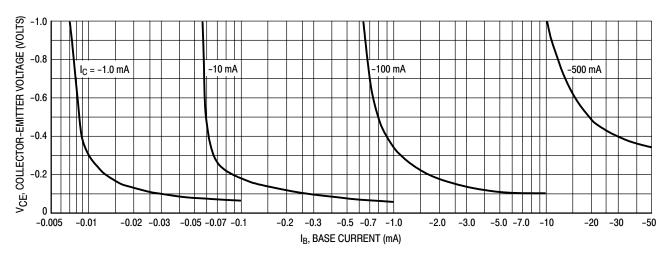


Figure 4. Collector Saturation Region

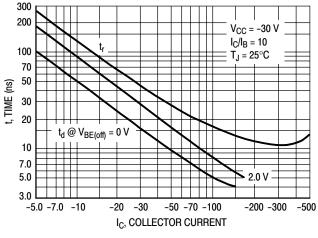


Figure 5. Turn-On Time

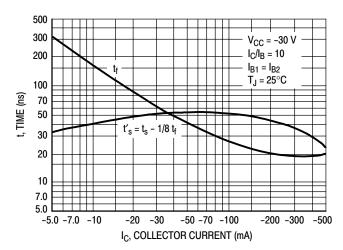
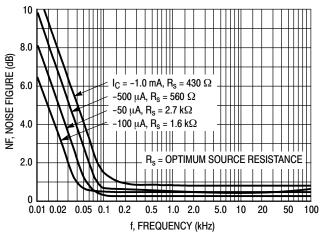


Figure 6. Turn-Off Time

# TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

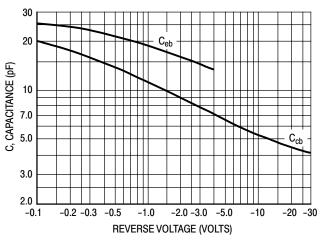
 $V_{CE}$  = 10 Vdc,  $T_A$  = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0 I<sub>C</sub> = -50 μA -100 μA -500 μA 4.0 2.0 100 200 2.0 k 5.0 k 10 k 20 k 50 k 50 1.0 k R<sub>s</sub>, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



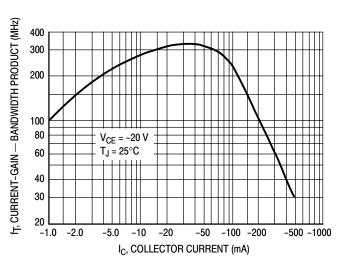
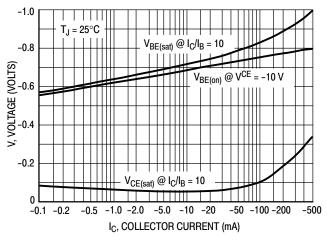


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



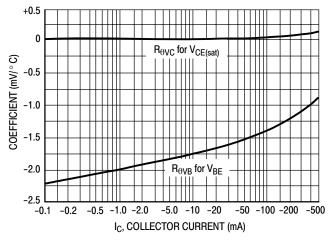


Figure 11. "On" Voltage

Figure 12. Temperature Coefficients

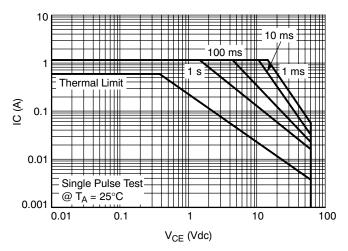
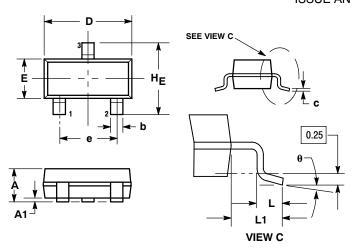


Figure 13. Safe Operating Area

# PACKAGE DIMENSIONS

# SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- 2. CONTROLLING DIMENSION. HOCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES
  LEAD FINISH THICKNESS. MINIMUM LEAD
  THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

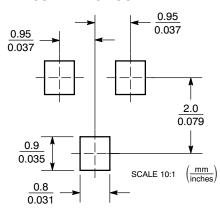
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6: PIN 1. BASE

2. EMITTER

COLLECTOR

# **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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